

# THICK FILM HYBRID INTEGRATED CIRCUIT MC-5157

### VHF~UHF BROAD-BAND AMPLIFIER

#### DESCRIPTION AND APPLICATIONS

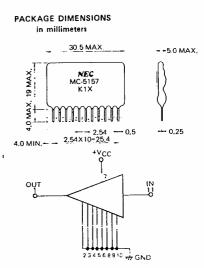
The MC-5157 is a thick film hybrid integrated circuit designed for broad-band general purpose amplifier applications in the 30 to 900 MHz band. The device is a "post amplifier" which features low noise, flat gain with a typical output of 100 to 110 dB $\mu$ V/75  $\Omega$ . Since the MC-5157 is designed to serve as a VHF-UHF TV booster amplifier, the device is matched to 75  $\Omega$ . The MC-5157 offers solutions to many amplifier problems where battery operation and bandwidth is required. Reliability and performance uniformity are assured by gold metallized transistors and NEC's stringent quality-control procedures. The MC-5157 is a complete circuit which requires no additional adjustments or components. Its use offers reductions in teh number of manufacturing operations, assembly time, parts control, maintenance and design complexity.

#### **FEATURES**

- Operates as a flat amplifier from 30 to 900 MHz without adjustments or external components.
- Input and output matching to 75  $\Omega$  .
- Low noise figure (4.5 dB TYP.)
- Low intermodulation distortion (IM2=-46 dB, IM3=-57 dB TYP.)

#### ABSOLUTE MAXIMUM RATINGS (Ta=25 °C)

Supply Voltage	Vcc	18	٧
Operating Current	Icc	75	mΑ
Input Voltage	$v_{1}$	0.5	٧
Total Dissipation	PΤ	1.3	W
Operating Temperature	$T_{opt}$	-30 to +65	°C
Storage Temperature	$T_{stg}$	-30 to +85	°C



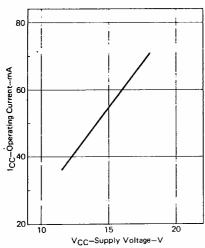
## ELECTRICAL CHARACTERISTICS (Ta=25 °C, V<sub>CC</sub>=+12 V, Z<sub>S</sub>=Z<sub>L</sub>=75 Ω)

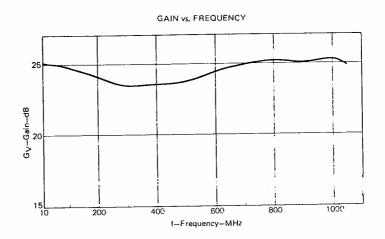
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CHARACTERISTIC	SYMBOL	· MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Operating Current	Icc	34	39	44	mA	
Average Gain	G∨(av)	24		25	dB	f=30~900 MHz
Gain Flatness	±G <sub>V</sub> (av)		1.0	1.2	dB	f=30~900 MHz
Input Output VSWR	VSWR <sub>I,O</sub>			2.5		f=30~900 MHz
Isolation	Iso	30			dB	f=30~900 MHz
Noise Figure	NF		4.5	5.0	dB	f=30~300 MHz
			4.8	5.5	dB	f=300~900 MHz
2nd Order Intermodulation	IM <sub>2</sub>		46	<b>-40</b>	dB	f <sub>1</sub> =90 MHz, f <sub>2</sub> =100 MHz,f=f <sub>1</sub> +f <sub>2</sub>
Distortion			<b>-51</b> *		dB	V <sub>O</sub> =100 dBμV/75 Ω
2nd Order Intermodulation Distortion	IM <sub>2</sub>		-43.5	-38	dB	f1=200 MHz, f2=500 MHz,f=f1+f2
	ļ		<del>-49*</del>		dB	V <sub>O</sub> =100 dBμV/75 Ω
3rd Order Intermodulation	IM <sub>3</sub>		<b>–</b> 57	-53	dB	f <sub>1</sub> =200 MHz, f <sub>2</sub> =210 MHz, f=2f <sub>1</sub> -f <sub>2</sub>
Distortion			-65*		dB	V <sub>O</sub> =100 dBμV/75 Ω

\*V<sub>CC</sub>=15 V

# TYPICAL CHARACTERISTICS (Ta=25 °C)







# INTERMODULATION DISSIPATION VS. SUPPLY VOLTAGE

